

#2

Sheet 1 of 2

Form 1449*	Atty. Docket No.: 303.684US2	Serial No. Unknown
	Applicant: Leonard Forbes	10/04/2924
	Filing Date: Herewith 01/09/02	Group: Unknown

2813  
11002/42924  
01/09/02

## U.S. PATENT DOCUMENTS

**Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
W.H.	3,387,286	06/04/1968	Dennard, R.H.	340	173	07/14/67
W.H.	3,882,469	05/06/1975	Gosney, Jr., W.M.	340	173R	06/18/73
W.H.	4,173,766	11/06/1979	Hayes, J.A.	357	23	09/16/77
W.H.	4,409,723	10/18/1983	Harari, E.	29	571	09/08/80
W.H.	4,435,785 ✓	03/06/1984	Chapman, R.A.	365	147	06/02/81
	5,020,030	05/28/1991	Huber, R.J.	365	185	10/31/88
	5,596,214	01/21/1997	Endo, N.	257	324	05/30/
	5,740,104	04/14/1998	Forbes, L.	365	185.03	01/29/97
	5,754,477	05/19/1998	Forbes, L.	365	185.33	01/29/97
	5,768,193	06/16/1998	Lee, P.W., et al.	365	185.25	11/07/96
	5,790,455	08/04/1998	Caywood, J.M.	365	185.96	01/02/97
	5,796,670	08/18/1998	Liu, K.	365	228	11/07/96
	5,801,401	09/01/1998	Forbes, L.	257	77	01/29/97
	5,811,865	09/22/1998	Hodges, R.L., et al.	257	411	12/16/96
	5,886,368	03/23/1999	Forbes, L., et al.	257	77	07/29/97
	6,011,725	01/04/2000	Eitan, B.	365	185.33	02/04/99
	6,025,627	02/15/2000	Forbes, L., et al.	257	321	05/29/98
	6,031,263	02/29/2000	Forbes, L., et al.	257	315	07/29/97
W.H.	6,063,668	05/16/2000	He, Y., et al.	438	264	12/18/97
W.H.	6,096,640	08/01/2000	Hu, Y.	438	652	04/02/98

## FOREIGN PATENT DOCUMENTS

**Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation Yes	No

## OTHER DOCUMENTS

(Including Author, Title, Date, Pertinent Pages, Etc.)

	Chen, I., et al., "A Physical Model for the Gate Current Injection in p-Channel MOSFET's", <u>IEEE Electron Device Letters</u> , 14(5), 228-230, (May 1993)
	Chen, J., et al., "Hot Electron Gate Current and Degradation in P-Channel SOI MOSFET's", <u>1991 IEEE International SOI Conference Proceedings</u> , Vail Valley, Colorado, pp.8-9, (October 1991)
	Chung, S.S., et al., "Performance and Reliability Evaluations of P-Channel Flash Memories with Different Programming Schemes", <u>International Electron Devices Meeting, Technical Digest</u> , Washington, D.C., 295-298, (December 1997)

Examiner

*Walter Allegre*

Date Considered

7-11-2003

\*Substitute Disclosure Statement Form (PTO-1449)

\*\*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Form 1449*	Atty. Docket No.: 303.684US2	Serial No. <u>Unknown</u>
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	Applicant: Leonard Forbes	<u>10/642 924</u>
	Filing Date: <u>Herewith 01/09/02</u>	Group: <u>Unknown 2813</u>

## OTHER DOCUMENTS

(Including Author, Title, Date, Pertinent Pages, Etc.)

\*\*Examiner  
Initial

- Dipert, B., et al., "Flash Memory Goes Mainstream", IEEE Spectrum, 30, 48-52, (October 1993)
- Ghodsi, R., et al., "Gate-Induced Drain-Leakage in Buried-Channel PMOS-A Limiting Factor in Development of Low-Cost, High-Performance 3.3-V, 0.25- $\mu$ m Technology", IEEE Electron Device Letters, 19(9), 354-356, (September 1998)
- Ohnakado, T., et al., "1.5V Operation Sector-Erasable Flash Memory with Bipolar Transistor Selected (BITS) P-Channel Cells", 1998 Symposium on VLSI Technology, Digest of Technical Papers, 14-15, (1998)
- Ohnakado, T., et al., "Novel Electron Injection Method Using Band-to-Band Tunneling-Induced Hot Electron (BBHE) for Flash Memory with a P-Channel Cell", 1995 International Electron Devices Meeting TECHNICAL DIGEST, Washington D.C., pp. 279-282, (1995)
- Ohnakado, T., et al., "Novel Self-Limiting Program Scheme Utilizing N-Channel Select Transistors in P-Channel DINOR Flash Memory", 1996 International Electron Devices Meeting TECHNICAL DIGEST, San Francisco, CA, pp. 181-184, (1996)
- Papadas, C., et al., "Modeling of the Intrinsic Retention Characteristics of FLOTOX EEPROM Cells Under Elevated Temperature Conditions", IEEE Transaction on Electron Devices, 42, 678-682, (April 1995)
- Patel, N.K., et al., "Stress-Induced Leakage Current in Ultrathin SiO<sub>2</sub> Films", Appl. Phys. Letters, 64(14), 1809-1811, (April 1994)
- Salm, C., et al., "Gate Current and Oxide Reliability in p+ Poly MOS Capacitors with Poly-Si and Poly-Ge0.3Si0.7 Gate Material", IEEE Electron Device Letters 19(7), 213-215, (July 1998)
- Shi, Y., et al., "Tunneling Leakage Current in Ultrathin (<4 nm) Nitride/Oxide Stack Dielectrics", IEEE Electron Device Letters, 19(10), pp. 388-390, (October 1998)
- Wu, Y., et al., "Time Dependent Dielectric Wearout (TDDW) Technique for Reliability of Ultrathin Gate Oxides", IEEE Electron Device Letters, 20(6), 262-264, (June 1999)

Examiner

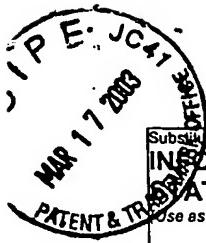
Hellegeen

Date Considered

7-11-03

\*Substitute Disclosure Statement Form (PTO-1449)

\*\*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.



PTO/SB/08A(10-01)  
Approved for use through 10/31/2002. OMB 0510-0031  
US Patent & Trademark Office, U.S. DEPARTMENT OF COMMERCE

#3

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449A/PTO  
**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**  
(use as many sheets as necessary)

Complete if Known

Application Number	10/042924
Filing Date	January 9, 2002
First Named Inventor	Forbes, Leonard
Group Art Unit	2822 2813
Examiner Name	Unknown VESPERMAN

Sheet 1 of 1

Attorney Docket No: 303.684US2

US PATENT DOCUMENTS

Examiner Initials*	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
LLW	US-6,008,091	12/28/1999	Gregor, R.W., et al.	438	261	01/27/1998
LLW	US-6,204,179	03/20/2001	McTeer, Allen	438	687	07/09/2002
LLW	US-6,207,222	03/27/2001	Chen, Liang-Yuh, et al.	427	97	08/24/1999
LLW	US-6,249,460	06/19/2001	Forbes, L., et al.	365	185.28	02/28/2000
LLW	US-6,319,774	11/20/2001	Hai, T.T.	438	259	02/27/1998

FOREIGN PATENT DOCUMENTS

Examiner Initials*	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	T <sup>2</sup>

OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>

RECEIVED  
MAR 19 2003  
TECHNOLOGY CENTER 2800

RECEIVED  
MAR 19 2003  
TECHNOLOGY CENTER 2800